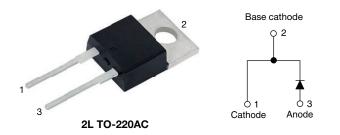
**Vishay Semiconductors** 

# 650 V Power SiC Merged PIN Schottky Diode, 6 A



www.vishay.com

## LINKS TO ADDITIONAL RESOURCES

30	SPICE	
3D Models	Models	Application Notes

PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	6 A				
V <sub>R</sub>	650 V				
V <sub>F</sub> at I <sub>F</sub> at 150 °C	1.70 V				
T <sub>J</sub> max.	175 °C				
I <sub>R</sub> at V <sub>R</sub> at 175 °C	4.4 µA				
Q <sub>C</sub> (V <sub>R</sub> = 400 V)	17 nC				
Package	2L TO-220AC				
Circuit configuration	Single				

## FEATURES

 Majority carrier diode using Schottky technology on SiC wide band gap material



COMPLIANT HALOGEN

FREE

- Positive V<sub>F</sub> temperature coefficient for easy paralleling
- · Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

## **DESCRIPTION / APPLICATIONS**

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

## **MECHANICAL DATA**

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

<b>ABSOLUTE MAXIMUM RATINGS</b>	$(T_A = 25 \circ 0)$	C unless otherwise specified)			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V <sub>RRM</sub>		650	V	
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 127 °C (DC)	6	А	
DC blocking voltage	V <sub>DC</sub>		650	V	
Repetitive peak surge current	I <sub>FRM</sub>	$T_C$ = 25 °C, f = 50 Hz, square wave, DC = 25 $\%$	23		
Non-repetitive peak forward surge current	I <sub>FSM</sub>	$T_C = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ half sine wave}$	39	А	
		$T_{C}$ = 110 °C, $t_{p}$ = 10 ms, half sine wave	37		
Devues disaination	P <sub>tot</sub> <sup>(1)</sup>	T <sub>C</sub> = 25 °C	42	w	
Power dissipation		T <sub>C</sub> = 110 °C	18	vv	
l <sup>2</sup> t value	∫i <sup>2</sup> dt	T <sub>C</sub> = 25 °C	8		
		T <sub>C</sub> = 110 °C	6.8	A <sup>2</sup> s	
Operating junction and storage temperatures	T <sub>J</sub> <sup>(2)</sup> , T <sub>Stg</sub>		-55 to +175	°C	

#### Notes

<sup>(1)</sup> Based on maximum R<sub>th</sub>

 $^{(2)}$  The heat generated must be less than the thermal conductivity from junction-to-ambient: dP\_D/dT\_J < 1/R\_{\rm 0JA}

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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP. MAX					
		I <sub>F</sub> = 6 A	-	1.45	1.70		
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A, T <sub>J</sub> = 150 °C	-	1.70	2.10	V	
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 175 °C	-	1.80	-		
		$V_{R} = V_{R}$ rated	-	-	35		
Reverse leakage current	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 150 °C	-	-	75	μA	
		V <sub>R</sub> = V <sub>R</sub> rated, T <sub>J</sub> = 175 °C	-	4.4	-		
Total conceitance	С	V <sub>R</sub> = 1 V, f = 1 MHz	-	250	-	pF	
Total capacitance	0	V <sub>R</sub> = 400 V, f = 1 MHz	-	27	-	μr	
Total capacitive charge	Q <sub>C</sub>	V <sub>R</sub> = 400 V, f = 1 MHz	-	17	-	nC	

<b>THERMAL - MECHANICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	2.55	3.6	°C/W
Marking device				C06E	T07T	

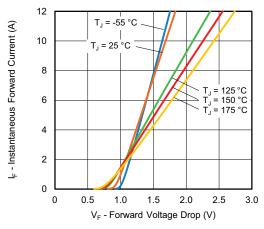


Fig. 1 - Typical Forward Voltage Drop Characteristics

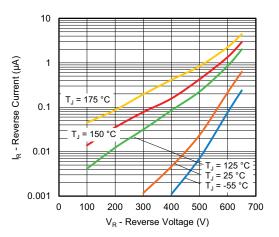


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

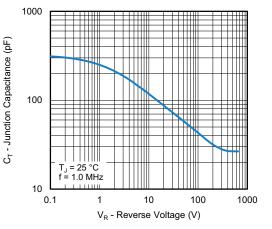


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

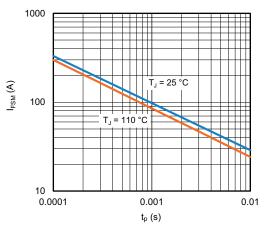
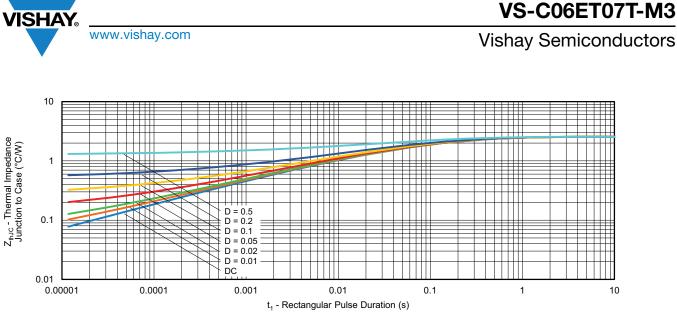
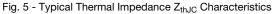


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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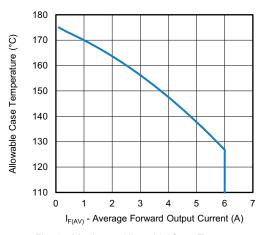


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

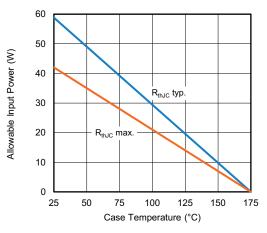


Fig. 7 - Forward Power Loss Characteristics

7 6 Capacitive Energy (µJ) 5 4 3 2 T<sub>J</sub> = 25 °C, f = 1.0 MHz 1 C V dV  $E_J =$ 0 0 100 200 300 400 500 600 700 Reverse Voltage (V)

Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

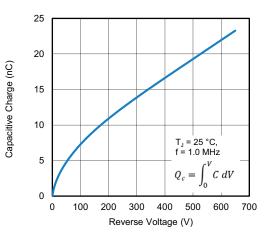


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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## **ORDERING INFORMATION TABLE**

Device code	VO			_	-	07	-	
Device code	VS-	С	06	E	Т	07	T	-M3
	1	2	3	4	5	6	7	8
	1	- Visl	nay Serr	niconduo	ctors pr	oduct		
	2	- C =	SiC dio	de				
	3	- Cur	rent rati	ng (06 =	= 6 A)			
	4	• E=	single c	diode				
	5	- Pac	kage T	D-220				
	6	- Vol	tage rati	ng: (07	= 650 V	)		
	7	• T =	true 2 p	in				
	8	- Env	ironmer	ntal digit	:			
		-M3	3 = halog	gen-free	e, RoHS	-compli	ant, and	d termir

ORDERING INFORMATION							
PREFERRED P/N	BASE QUANTITY	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-C06ET07T-M3	50/tube	1000	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?96069		
Part marking information	www.vishay.com/doc?95391		
SPICE model	www.vishay.com/doc?96830		



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